

Product Overview

N93C66: CMOS EEPROM Memory, 4 Kb, Serial, Microwire

For complete documentation, see the data sheet.

The N93C66 is a 4-kb CMOS Serial EEPROM device which is organized as either 256 registers of 16 bits (ORG pin at V_{CC}) or 512 registers of 8 bits (ORG pin at GND). Each register can be written (or read) serially by using the DI (or DO) pin. The N93C66 features sequential read and self-timed internal write with auto-clear. On-chip Power-On Reset circuitry protects the internal logic against powering up in the wrong state.

Features

- High Speed Operation: 4 MHz
- Low Power CMOS Technology
- 1.7 V to 5.5 V Supply Voltage Range
- Selectable x8 or x16 Memory Organization
- Sequential Read
- Software Write Protection
- Power-up Inadvertent Write Protection
- 1,000,000 Program/Erase Cycles
- 100 Year Data Retention
- Industrial Temperature Range

For more features, see the data sheet

Applications

- Communications Systems
- Computer Systems
- Consumer Systems
- Industrial Systems

Part Electrical Specifications

Product	Compliance	Status	Type	Density	Organization	Data Transmission Standard	f_{cycle} Max (kHz)	t_{ACC} Max ns	V_{CC} Min (V)	V_{CC} Max (V)	$I_{standby}$ Max (μ A)	I_{act} Max (mA)	T Min ($^{\circ}$ C)	T Max ($^{\circ}$ C)	Package Type
N93C66BT3ETAG	Pb-free Halide free	Active	Serial	4 kb	512k x 8	Micro Wire	4,000	250	1.7	5.5	2	1	-40	85	TDFN-8

For more information please contact your local sales support at www.onsemi.com.

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